

Abstract of the Disclosure:

A circuit structure has at least two etching trenches disposed at sidewalls of a silicon block left behind during the etching of the structure. The etching trenches are disposed at angles  
5 with respect to one another that are prescribed by the form of the silicon block left behind. Semiconductor layer structures which can interact with one another diagonally across are in each case accommodated in the etching trenches. In this case, the function of the entire circuit structure results from the  
10 interaction of the layer structures disposed in the various etching trenches.

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